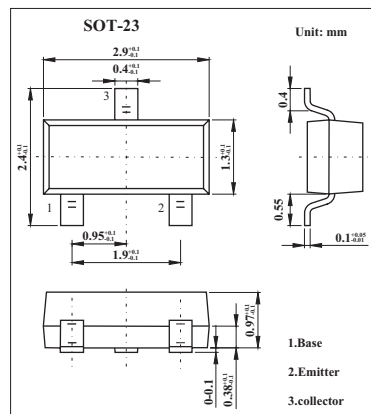


FMMT5210

■ Features

- Small signal transistor.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	4.5	V
Collector current	I _c	50	mA
Power dissipation	P _{tot}	330	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cut-off current	I _{cBO}	V _{CB} =35V, I _E =0			50	nA
Emitter-base current	I _{EBO}	V _{EB} =3V, I _C =0			50	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA			700	mV
Base-emitter ON voltage	V _{BE(on)}	I _C =1mA, V _{CE} =5V			850	mV
Static Forward Current Transfer Ratio	h _{FE}	I _C =100μA, V _{CE} =5V	200		600	
Current-gain-bandwidth product	f _T	I _C =0.5mA, V _{CE} =5V, f=20MHz	30			MHz
Small signal current transfer ratio	h _{fe}	I _C =1mA, V _{CE} =5V, f=1KHz	250		900	
Noise figure	NF	I _C =200μA, V _{CE} =5V, R _g =2KΩ, f=30Hz to 15KHz at -3dB points			2	dB
		I _C =200μA, V _{CE} =5V, R _g =2KΩ, f=1KHz to Δf=200Hz			3	dB
Output capacitance	C _{obo}	V _{CB} =5V, I _E =0, f=140KHz			4	pF

■ Marking

Marking	2R
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